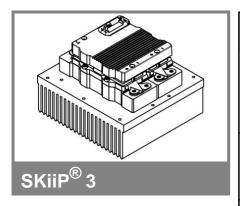
## SKiiP 1213GB123-2DL



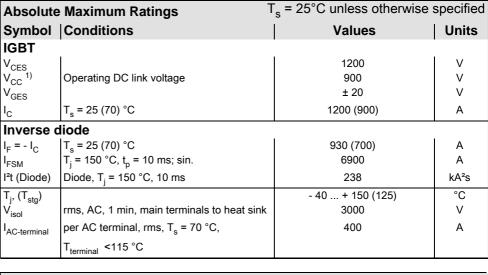
## 2-pack-integrated intelligent Power System

### Power section SKiiP 1213GB123-2DL

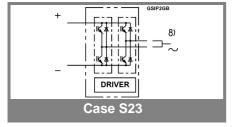
Data

#### **Power section features**

- SKiiP technology inside
- Trench IGBTs
- CAL HD diode technology
- · Integrated current sensor
- · Integrated temperature sensor
- Integrated heat sink
- IEC 60721-3-3 (humidity) class 3K3/IE32 (SKiiP<sup>®</sup> 3 System)
- IEC 60068-1 (climate) 40/125/56)
- UL recognized file no. E63532
- with assembly of suitable MKP capacitor per terminal
- 8) AC connection busbars must be connected by the user; copper busbars available on request



Characteristics				T <sub>s</sub> = 25°C unless otherwise specified					
Symbol	Conditions				min.	typ.	max.	Units	
IGBT									
V <sub>CEsat</sub>	I <sub>C</sub> = 600 A measured at t	, T <sub>j</sub> = 25 (1 erminal	25) °C;			1,7 (1,9)	2,1	V	
$V_{CEO}$	$T_i = 25 (12)$	.5) °C; at to	erminal			0,9 (0,8)	1,1 (1)	V	
$r_{CE}$	$T_j = 25 (12)$					1,3 (1,8)	1,7 (2,2)	mΩ	
I <sub>CES</sub>	$V_{GE} = 0 \text{ V},$ $T_i = 25 (12)$		ES'			2,4 (72)		mA	
$E_{on} + E_{off}$	$I_{\rm C} = 600  {\rm A}$	$V_{CC} = 60$	0 V			mJ			
	T <sub>j</sub> = 125 °C					mJ			
R <sub>CC+EE</sub>	terminal ch	nip, T <sub>j</sub> = 25	°C			mΩ			
L <sub>CE</sub>	top, botton	n				nH			
C <sub>CHC</sub>	per phase,	AC-side				3,4		nF	
Inverse o	diode								
$V_F = V_{EC}$	I <sub>F</sub> = 600 A <sub>1</sub> measured at t		25) °C			1,5 (1,5)	1,8	V	
$V_{TO}$	T <sub>i</sub> = 25 (12	25) °C				0,9 (0,7)	1,1 (0,9)	V	
r <sub>T</sub>	$T_i = 25 (12)$					1 (1,3)	1,1 (1,5)	mΩ	
E <sub>rr</sub>	$I_{\rm C} = 600  \text{A}$	I <sub>C</sub> = 600 A, V <sub>CC</sub> = 600 V				42		mJ	
	T <sub>j</sub> = 125 °C, V <sub>CC</sub> = 900 V					mJ			
Mechani	cal data								
$M_{dc}$	DC termina	-			6		8	Nm	
M <sub>ac</sub>	AC termina				13		15	Nm kg	
W		SKiiP® 3 System w/o heat sink				1,7			
W		heat sink 5,4 kg							
Thermal characteristics (PX16 heat sink with fan SKF16B-230-1); "s" reference to heat sink; "r" reference to built-in temperature sensor (acc. IEC 60747-15)									
R <sub>th(i-s)I</sub>	per IGBT						0,03	K/W	
R <sub>th(j-s)D</sub>	per diode						0,058	K/W	
Z <sub>th</sub>	R <sub>i</sub> (mK/W) (max. values)				ı	1			
	1	2	3	4	1	2	3	4	
$Z_{th(j-r)I}$	9,8	16,4	3,8	0	0,37	0,06	0,01	1	
$Z_{th(j-r)D}$	10	24	24	36	50	5	0,25	0,04	



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2,3

160

53

0,4

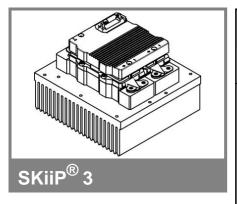
20,3

7,1

4,3

 $Z_{th(r-\underline{a})}$ 

## SKiiP 1213GB123-2DL



# 2-pack-integrated intelligent Power System

2-pack integrated gate driver SKiiP 1213GB123-2DL

Data

#### **Gate driver features**

- CMOS compatible inputs
- Wide range power supply
- Integrated circuitry to sense phase current, heat sink temperature and

DC-bus voltage (option)

- Short circuit protection
- · Over current protection
- Over voltage protection (option)
- Power supply protected against under voltage
- Interlock of top/bottom switch
- Isolation by transformers
- Fibre optic interface (option for GB-types only)
- IEC 60068-1 (climate) 40/85/56
- UL recognized file no. 242581

Absolute	Maximum Ratings	Γ <sub>a</sub> = 25°C unless otherwise specified		
Symbol	Conditions	Values	Units	
$V_{S2}$	unstabilized 24 V power supply	30	V	
$V_{i}$	input signal voltage (high)	15 + 0,3	V	
dv/dt	secondary to primary side	75	kV/μs	
$V_{isollO}$	input / output (AC, rms, 2s)	3000	V	
V <sub>isoIPD</sub>	partial discharge extinction voltage, rms, Q <sub>PD</sub> ≤10 pC;	1170	V	
V <sub>isol12</sub>	output 1 / output 2 (AC, rms, 2s)	1500	V	
f <sub>sw</sub>	switching frequency	15	kHz	
f <sub>out</sub>	output frequency for I <sub>peak(1)</sub> =I <sub>C</sub>	15	kHz	
$T_{op} (T_{stg})$	operating / storage temperature	- 40 + 85	°C	

Characte	eristics	(T <sub>a</sub> = 25 °			
Symbol	Conditions	min.	typ.	max.	Units
$V_{S2}$	supply voltage non stabilized	13	24	30	V
I <sub>S2</sub>	V <sub>S2</sub> = 24 V	278+25*f/kHz+0,00022*(I <sub>AC</sub> /A) <sup>2</sup>			mA
V <sub>iT+</sub>	input threshold voltage (High)	12,3		12,3	V
$V_{iT-}$	input threshold voltage (Low)	4,6			V
R <sub>IN</sub>	input resistance		10		kΩ
C <sub>IN</sub>	input capacitance		1		nF
t <sub>d(on)IO</sub>	input-output turn-on propagation time		1,3		μs
t <sub>d(off)IO</sub>	input-output turn-off propagation time	1,3			μs
t <sub>pERRRESET</sub>	error memory reset time	9			μs
$t_{TD}$	top / bottom switch interlock time		3,3		μs
I <sub>analogOUT</sub>	max. 5mA; 8 V corresponds to 15 V supply voltage for external components		1200		Α
I <sub>s1out</sub>	max. load current			50	mA
I <sub>TRIPSC</sub>	over current trip level (I <sub>analog</sub> OUT = 10 V)	110	1500	100	A
T <sub>tp</sub>	over temperature protection	110		120	°C
U <sub>DCTRIP</sub>	U <sub>DC</sub> -protection ( U <sub>analog OUT</sub> = 9 V);		not implemented	d	V
	(option for GB types)				

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